	Application No.	pplication No. Applicant(s)	
Notice of Allowability	10/670,037	/670,037 BURKE ET AL.	
	Examiner	Art Unit	
	Michael Trinh	2822	
The MAILING DATE of this communication app All claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85 NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT F of the Office or upon petition by the applicant. See 37 CFR 1.31	S (OR REMAINS) CLOSED (i) or other appropriate commregistric application is 3 and MPEP 1308.	in this application. If not include nunication will be mailed in due	ed course. <b>THIS</b>
1. This communication is responsive to <u>Amendment filed Ju</u>	<u>ne 27, 2005</u> .		
2. X The allowed claim(s) is/are 1,3,4,6-8 and 10-22.			
3. X The drawings filed on 24 September 2003 are accepted by	y the Examiner.		
<ul> <li>4. Acknowledgment is made of a claim for foreign priority to a) All b) Some* c) None of the:</li> <li>1. Certified copies of the priority documents have</li> <li>2. Certified copies of the priority documents have</li> <li>3. Copies of the certified copies of the priority documents have International Bureau (PCT Rule 17.2(a)).</li> <li>* Certified copies not received:</li> </ul>	re been received. re been received in Applicati	on No	lion from the
Applicant has THREE MONTHS FROM THE "MAILING DATE noted below. Failure to timely comply will result in ABANDON THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.	of this communication to fil MENT of this application.	e a reply complying with the req	luirements
5. A SUBSTITUTE OATH OR DECLARATION must be subr INFORMAL PATENT APPLICATION (PTO-152) which giv			OTICE OF
<ol> <li>CORRECTED DRAWINGS ( as "replacement sheets") mu(a) including changes required by the Notice of Draftsper 1) hereto or 2) to Paper No./Mail Date</li> <li>(b) including changes required by the attached Examiner Paper No./Mail Date</li> <li>Identifying indicia such as the application number (see 37 CFR each sheet. Replacement sheet(s) should be labeled as such in 7. DEPOSIT OF and/or INFORMATION about the deposition of the page of the property of the page of th</li></ol>	rson's Patent Drawing Revie 	or in the Office action of the drawings in the front (not the FR 1.121(d).	•
attached Examiner's comment regarding REQUIREMENT	FOR THE DEPOSIT OF BI	OLOGICAL MATERIAL.	ioto tric
Attachment(s)  1. ☐ Notice of References Cited (PTO-892)  2. ☐ Notice of Draftperson's Patent Drawing Review (PTO-948)	6. ☐ Interview S Paper No.	nformal Patent Application (PTC Summary (PTO-413), /Mail Date	)-152)
<ol> <li>Information Disclosure Statements (PTO-1449 or PTO/SB/ Paper No./Mail Date</li> </ol>		Amendment/Comment	
4. Examiner's Comment Regarding Requirement for Deposit		Statement of Reasons for Alloy	wance
of Biological Material	9. ☐ Other	- Jul	21
		Michae Primary E	

Application/Control Number: 10/670,037 Page 2

Art Unit: 2822

## **DETAILED ACTION**

\*\*\* This office action is in response to Applicant's Amendment filed June 27, 2005. Claims 2,5,9,23-34 were canceled. Claims 1,3-4,6-8,10-22 are pending.

## Allowable Subject Matter

- 1. Claims 1,3-4,6-8,10-22 are allowed.
- 2. The following is a statement of reasons for the indication of allowable subject matter:

In the amendment filed June 27, 2005, Applicant rewrites objected claim 9 into independent form to include all of the limitations of the base claims and any intervening claims. Accordingly, pending claims 1,3-4,6-8,10-22 are allowed for reasons as of record. As of record, the references including Kim (5,851,868), Wu (5,998,264), etc., alone or in combination, do not anticipatively disclose each and every aspect of the claimed capacitive structure, or fairly make a prima facie obvious case of the claimed capacitive structure, in combination with other claimed limitations, and the inclusion of limitations of a polysilicon layer adjacent the first dielectric layer, wherein the well formed within the semiconductor base region, the first dielectric layer, and the first polysilicon layer form a first capacitor and are aligned along a planar dimension; a first conductive layer positioned with at least a portion overlying at least a portion of the polysilicon layer and electrically connected to said polysilicon layer; a second dielectric layer adjacent the first conductive layer; and a second conductive layer adjacent the second dielectric layer with a first electrical connection to said well, wherein the first conductive layer, the second dielectric layer, and the second conductive layer form a second capacitor and are aligned along the planar dimension; and said first electrical connection further comprising: a first metal layer comprising a first region and a second region electrically separate from the first region, wherein the first region is adjacent the second conductive layer; a second metal layer at a distance greater than a distance between the upper surface and the first region of the first metal layer; a second electrical connection between the first region of the first metal layer and the second metal layer; a third electrical connection between the second metal layer and the second region of the first metal layer; and a fourth electrical connection between the second region of the first metal layer and the well.

\*\*\*\*\*\*

Art Unit: 2822

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Michael M. Trinh whose telephone number is (571) 272-1847. The examiner can normally be reached on M-F: 8:30 Am to 5:00 Pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Amir Zarabian can be reached on (571) 272-1852. The fax phone numbers for the organization where this application proceeding is (703) 872-9306.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 308-0956. Oacs-16

Michael Trinh Primary Examiner